6.5 mΩ, Bidirectional Battery Switch in Compact WCSP

DESCRIPTION

The SiP32102 bidirectional switch feature reverse blocking capability to isolate the battery from the system. The internal switch has an ultra low 6.5 mΩ (typ at 3.3 V) on-resistance and operates from a +2.3 V to +5.5 V input voltage range, making the devices ideal battery-disconnect switches for high capacity battery applications.

The SiP32102 has slew rate control, making it ideal in large load capacitor as well as high current load switching applications. This device is also highly efficient, consuming only 110 nA (typ.) current in shutdown and while operating.

The SiP32102 has an active high enable. It can interface directly with a low voltage control signal.

The SiP32102 is available in an ultra compact 12-bump, 1.3 mm x 1.7 mm, 0.4 mm pitch WCSP package with top side lamination. The device operates over the temperature of -40 °C to +85 °C.

FEATURES

- Bidirectional on and off
- 7 A continuous current capability
- Ultra low R_{on}, 6.5 mΩ (typ.) at 3.3 V
- Wide input voltage, 2.3 V to 5.5 V
- Slew rate controlled turn on
- Low quiescent current: 110 nA
- EN pin with integrated pull up or pull down resistor
- Compact 12-bump, 1.3 mm x 1.7 mm x 0.55 mm WCSP package
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Pb-free

RoHS COMPLIANT

HALOGEN FREE

APPLICATIONS

- Smartphones and tablets
- Digital still / video cameras
- Portable meters and test instruments
- Communication devices with embedded batteries
- Portable medical and healthcare systems
- Data storage
- Battery bank

TYPICAL APPLICATION CIRCUIT

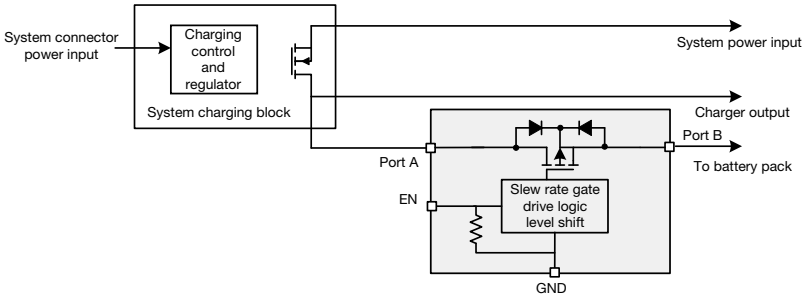


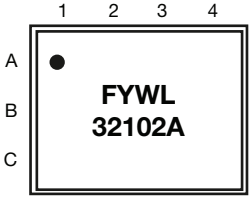
Fig. 1 - Typical Application Circuit

ORDERING INFORMATION					
PART NUMBER	MARKING	ENABLE	ENABLE PULL RESISTOR	PACKAGE	TEMPERATURE
SiP32102DB-T1-GE1	32102A	High	Enable pull Low	12-bump, 1.3 mm x 1.7 mm, 0.4 mm pitch WCSP package	-40 °C to +85 °C
SiP32102DB-T5-GE1	32102A	High	Enable pull Low		
SiP32102EVB	-	-	-	Evaluation board	-

Note

- GE1 denotes halogen-free and RoHS-compliant

MARKING



ABSOLUTE MAXIMUM RATINGS

PARAMETER	CONDITIONS	LIMIT	UNIT
V_{PA}, V_{PB}	Reference to GND	-0.3 to +6	V
	Pulse at 1 ms reference to GND [a]	-1.6	
V_{EN}	Reference to GND	-0.3 to +6	
Maximum Continuous Switch Current		7	A
Maximum Pulse Current	100 µs pulse	15	
ESD (HBM)		8000	V
Operating Temperature		-40 to +85	°C
Operating Junction Temperature		125	
Storage Temperature		-65 to +150	
Thermal Resistance (θ_{JA}) [b]		73	°C/W
Power Dissipation (P_D) [b, c]	T_A = 70 °C	1096	mW

Notes

a. Negative current injection up to 300 mA
b. All bumps soldered to 1" x 1", 2 oz. copper, 4 layers PC board
c. Derate 13.7 mW/°C above T_A = 70 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating/conditions for extended periods may affect device reliability.

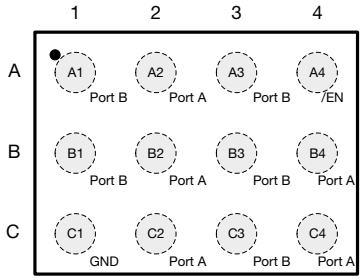
SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS UNLESS SPECIFIED V_{IN} = V_{PA}/V_{PB} = 2.3 V to 5.5 V, T_A = -40 °C to +85 °C (Typical values are at V_{PA}, V_{PB} = 4.2 V, C_{PA}, C_{PB} = 0.1 µF, T_A = 25 °C)	LIMITS MIN. [a]	 TYP. [b]	 MAX. [a]	UNIT
Power Supply						
Operating voltage [c]	$V_{PA/PB}$		2.3	-	5.5	V
Quiescent current	I_Q	V_{EN} = V_{IN}, no load	-	110	400	nA
Shutdown current	I_{SHDN}	V_{EN} = 0 V, no load	-	110	400	nA
Internal FET						
On-resistance	$R_{DS(on)}$	V_{PA}/V_{PB} = 2.3 V, I_L = 500 mA, T_A = 25 °C	-	8	13	mΩ
		V_{PA}/V_{PB} = 3.3 V, I_L = 500 mA, T_A = 25 °C	-	6.5	10	
Control						
EN input logic-low voltage [c]	V_{IL}		-	-	0.4	V
EN input logic-high voltage [c]	V_{IH}		1.4	-	-	
EN input logic hysteresis	$V_{I(HYS)}$		-	> 200	-	mV
EN pull resistor	R_{EN}	V_{PA}/V_{PB} = 5.5 V, $V_{\overline{EN}}$ (or V_{EN}) = 2.3 V	-	500	700	kΩ
Timing						
Output turn-on delay time	$t_{d(on)}$	V_{IN} = 4.2 V, R_L = 100 Ω, C_L = 0.1 µF, T_A = 25 °C	-	0.8	-	ms
Output turn-on rise time	t_r		-	1	-	
Output turn-off delay time	$t_{d(off)}$		-	0.12	-	
Output turn-off fall time	t_f		-	0.1	-	

Notes

a. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum
b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
c. For V_{IN} outside this range consult typical $\overline{EN}$, EN threshold curve

BUMP CONFIGURATION

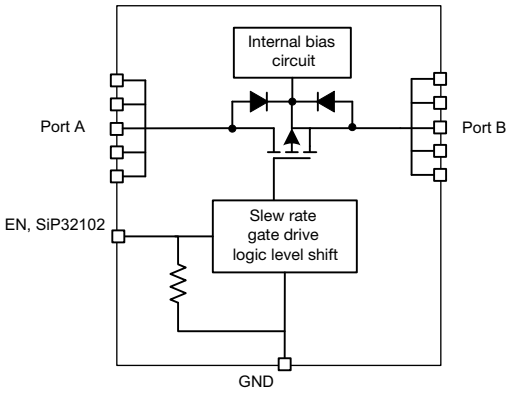


Top view
(solder bumps on bottom)

Fig. 2 - WCSP12, 1.3 mm x 1.7 mm

BUMP DESCRIPTION		
BUMP NUMBER	**NAME**	**FUNCTION**
A1, B1, A3, B3, C3	PB	Power port B
C1	GND	Ground
A2, B2, C2, B4, C4	PA	Power port A
A4	EN	Switch enable input, active high

FUNCTIONAL BLOCK DIAGRAM



TYPICAL CHARACTERISTICS (internally regulated 25 °C, unless otherwise noted)

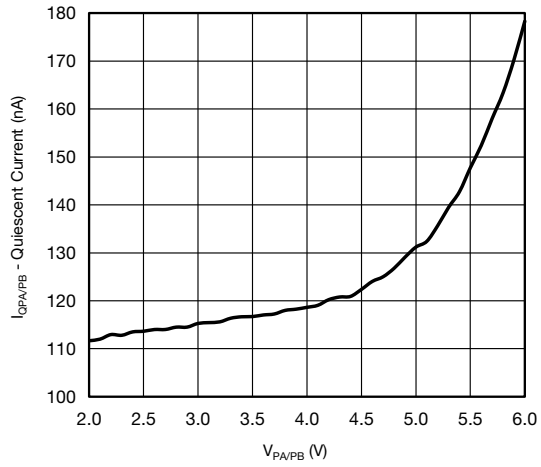


Fig. 3 - Quiescent vs. Input Voltage

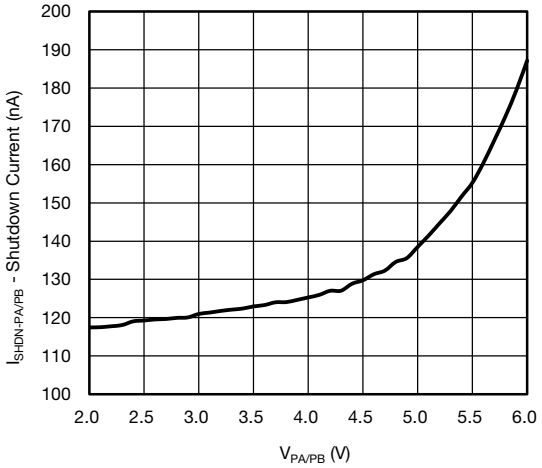


Fig. 4 - Shutdown Current vs. Input Voltage

TYPICAL CHARACTERISTICS (internally regulated 25 °C, unless otherwise noted)

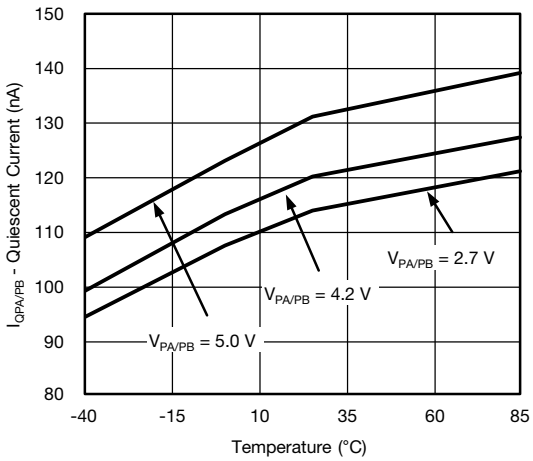


Fig. 5 - Quiescent vs. Temperature

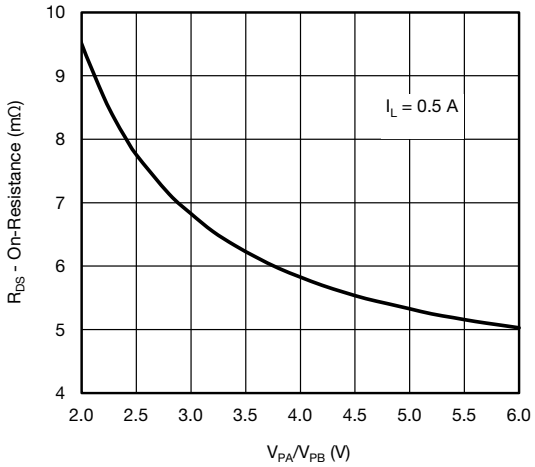


Fig. 8 - On Resistance vs. Input Voltage

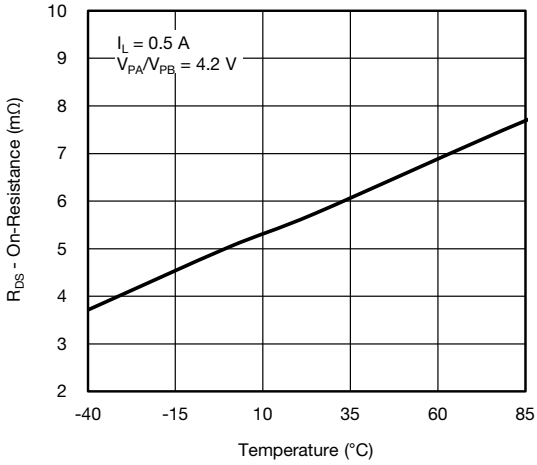


Fig. 6 - On Resistance vs. Temperature

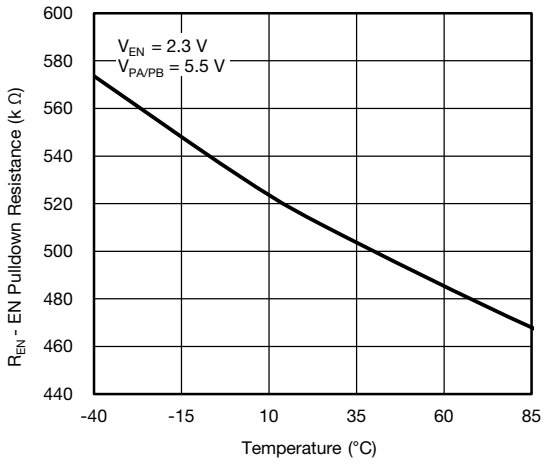


Fig. 9 - EN Pull down Resistance vs. Temperature

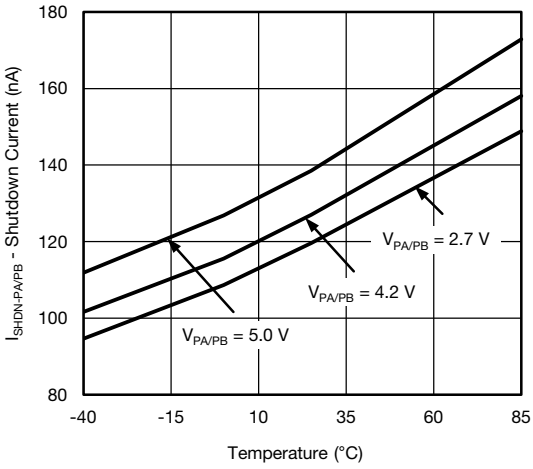


Fig. 7 - Shutdown Current vs.Temperature

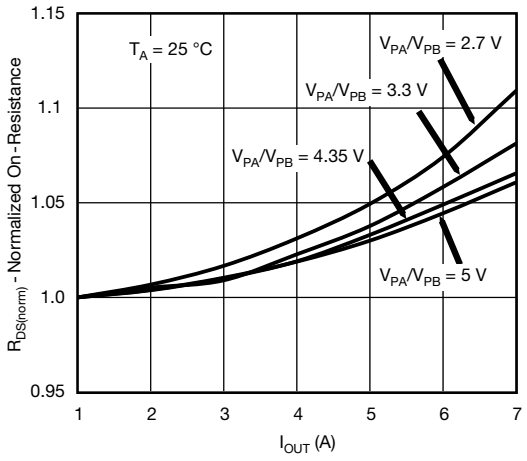


Fig. 10 - Normalized On Resistance vs. Load Current

TYPICAL CHARACTERISTICS (internally regulated 25 °C, unless otherwise noted)

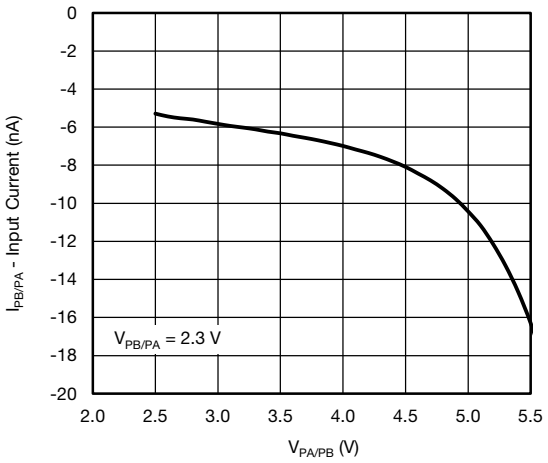


Fig. 11 - Reverse Blocking Current (I_{RB}) vs. Output Voltage

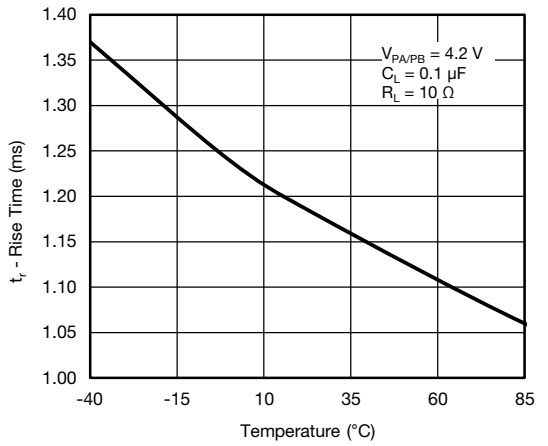


Fig. 12 - Rise Time vs. Temperature

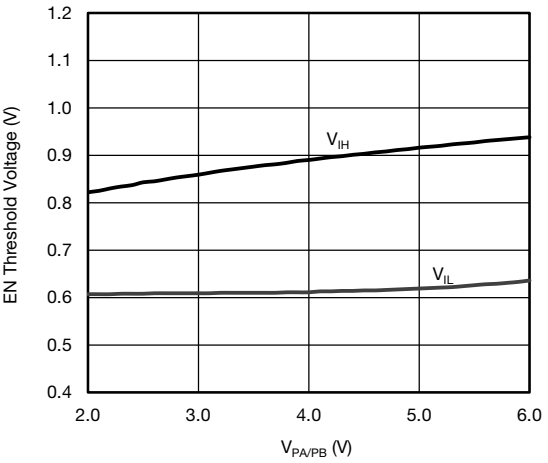


Fig. 13 - EN Threshold Voltage vs. Input Voltage

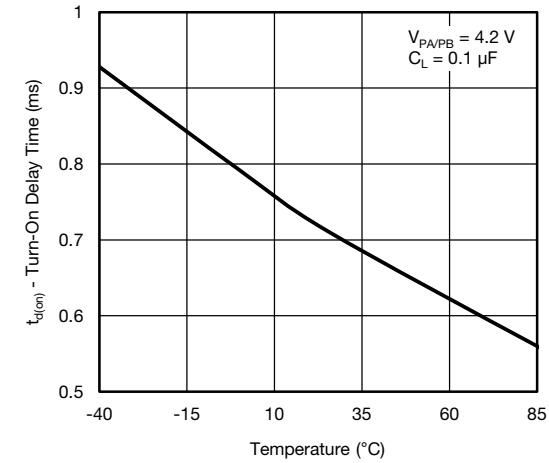


Fig. 14 - Turn-on Delay Time vs. Temperature

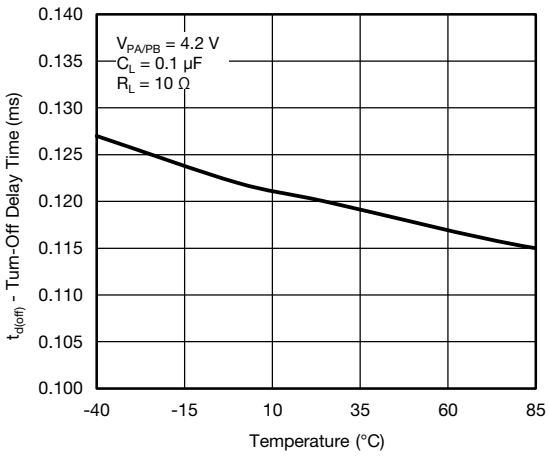


Fig. 15 - Turn-off Delay Time vs. Temperature

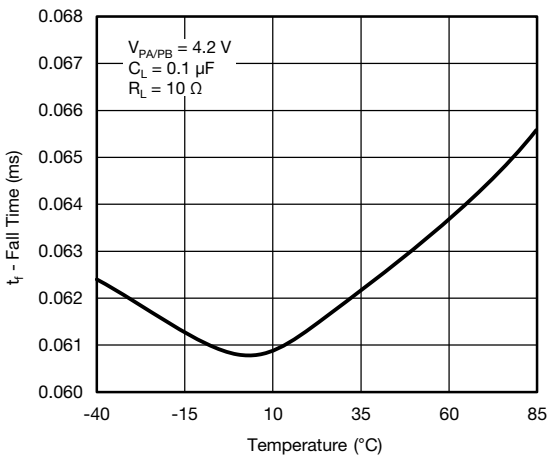


Fig. 16 - Fall Time vs. Temperature

DETAILED DESCRIPTION

The SiP32102 bidirectional switch features reverse blocking capability to isolate the battery from the system. The internal switch has an ultra low 6.5 mΩ (typ. at 3.3 V) on-resistance and operates from a +2.3 V to +5.5 V input voltage range, making the device ideal battery-disconnect switch for high capacity battery applications. The parts can handle 7 A continuous current at both directions.

The SiP32102 has slew rate control, making it ideal in large load capacitor as well as high current load switching applications.

The SiP32102 is available in an ultra compact 12-bump, 1.3 mm x 1.7 mm, 0.4 mm pitch WCSP package with top side lamination. The device operates over the temperature of -40 °C to +85 °C.

REVERSE CURRENT BLOCKING

The SiP32102 is a bidirectional switch that prevent current flowing from either port to the other when the device is disabled.

EN INPUT

The SiP32102 has an active-high enable pin that turns the switch on when high and off when low. The SiP32102 has an integrated pull down resistor at EN pin.

SWITCH ON AND OFF PERFORMANCE

The SiP32102 has a slew rate control. This minimizes the inrush current and provides a soft turn on.

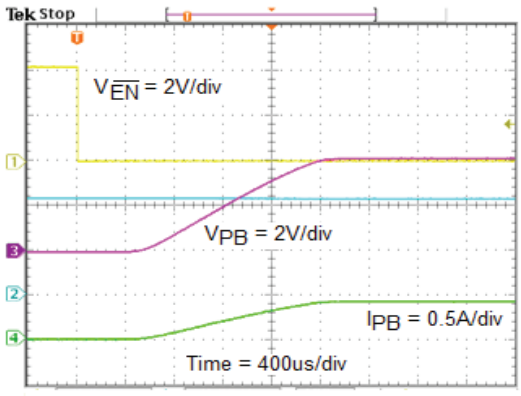


Fig. 17 - Port B Turn-On Time
(V_{PA} = 4.2 V, R_L = 10 Ω, C_L = 0.1 µF)

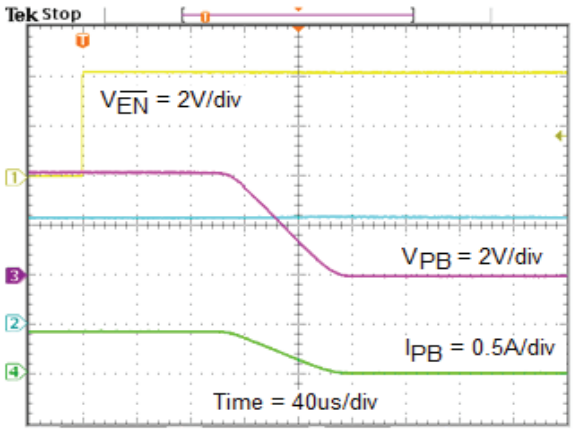


Fig. 18 - Port B Turn-Off Time
(V_{PA} = 4.2 V, R_L = 10 Ω, C_L = 0.1 µF)

DEVICE PIN OUT

Device pin out is designed for ease of layout.

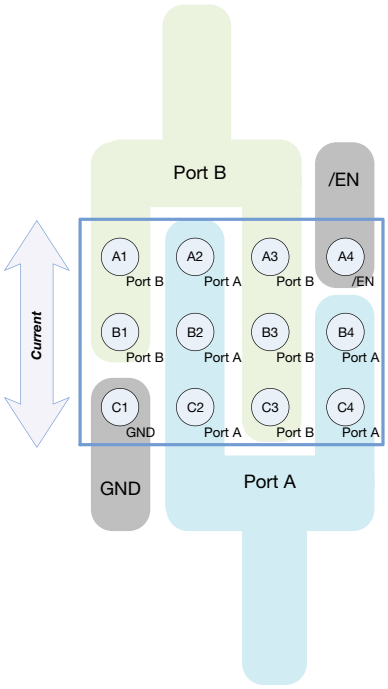
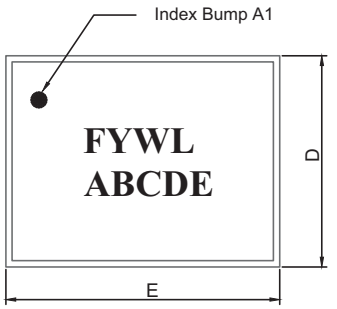


Fig. 19 - Proposed Layout

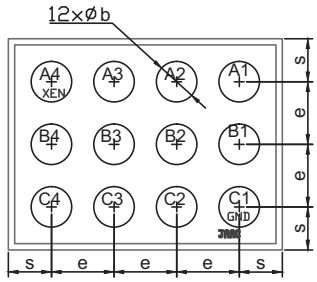
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?78809.

WCSP12: 12 Bumps

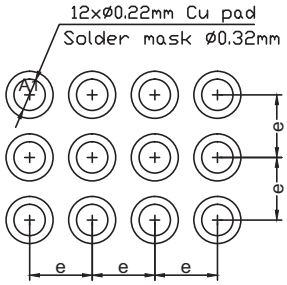
(3 x 4, 0.4 mm pitch, 208 µm bump height, 1.71 mm x 1.31 mm die size)



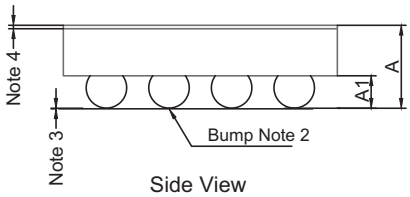
Top View



Bottom View



RECOMMENDED
LAND PATTERN
(NSMD)



Side View

DIMENSION	MILLIMETERS (5)			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.515	0.530	0.545	0.0203	0.0209	0.0215
A1	0.183	0.208	0.233	0.0072	0.0082	0.0092
b	0.234	0.260	0.312	0.0092	0.0102	0.0123
e		0.400			0.0157	
s	0.235	0.255	0.275	0.0093	0.0100	0.0108
D	1.270	1.310	1.350	0.0500	0.0516	0.0531
E	1.670	1.710	1.750	0.0657	0.0673	0.0689

Notes (unless otherwise specified)

(1) Laser mark on the silicon die back coated with an epoxy film.
(2) Bumps are SAC396.
(3) 0.050 max. co-planarity.
(4) Laminate tape thickness is 0.022 mm.
(5) Use millimeters as the primary measurement.

ECN: S13-2510-Rev. B, 16-Dec-13
DWG: 6017

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